Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of http://www.nxp.com, http://www.philips.com/ or http://www.semiconductors.philips.com/, use **http://www.nexperia.com**

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:
- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved
Should be replaced with:
- **© Nexperia B.V. (year). All rights reserved**.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

PEMD3; PIMD3; PUMD3

NPN/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

Rev. 11 — 25 September 2013 Product data sheet

1. Product profile

1.1 General description

NPN/PNP Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP complement	NPN/NPN complement	Package configuration
	NXP	JEITA			
PEMD3	SOT666	-	PEMB11	PEMH11	ultra small and flat lead
PIMD3	SOT457	SC-74	-	-	small
PUMD3	SOT363	SC-88	PUMB11	PUMH11	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

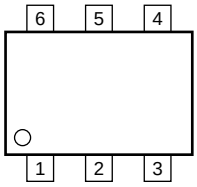
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor; for the PNP transistor (TR2) with negative polarity						
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I_O	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	

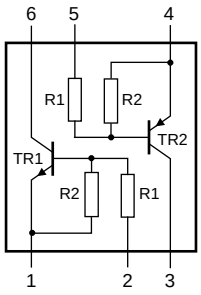
2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		



001aab555



006aaa143

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMD3	-	plastic surface-mounted package; 6 leads	SOT666
PIMD3	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457
PUMD3	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PEMD3	D3
PIMD3	M7
PUMD3	D*3

[1] * = placeholder for manufacturing site code.

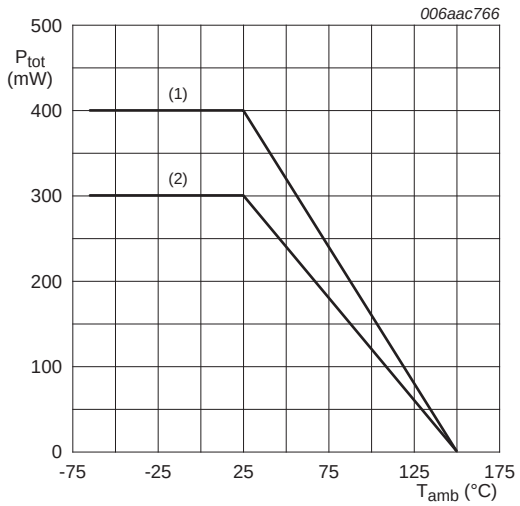
5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor; for the PNP transistor (TR2) with negative polarity						
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
V_I	input voltage TR1					
	positive			-	+40	V
	negative			-	–10	V
	input voltage TR2					
	positive			-	+10	V
	negative			-	–40	V
I_O	output current			-	100	mA
I_{CM}	peak collector current			-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]			
	PEMD3 (SOT666)			-	200	mW
	PIMD3 (SOT457)			-	250	mW
	PUMD3 (SOT363)			-	200	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]			
	PEMD3 (SOT666)			-	300	mW
	PIMD3 (SOT457)			-	400	mW
	PUMD3 (SOT363)			-	300	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–65	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



(1) SOT457; FR4 PCB, standard footprint

(2) SOT363 and SOT666; FR4 PCB, standard footprint

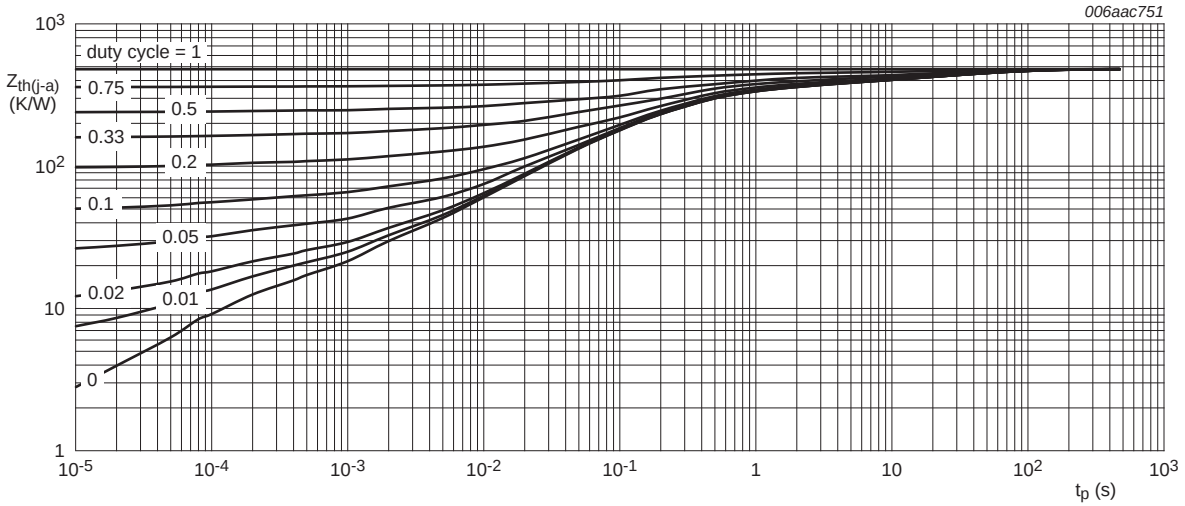
Fig 1. Per device: Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

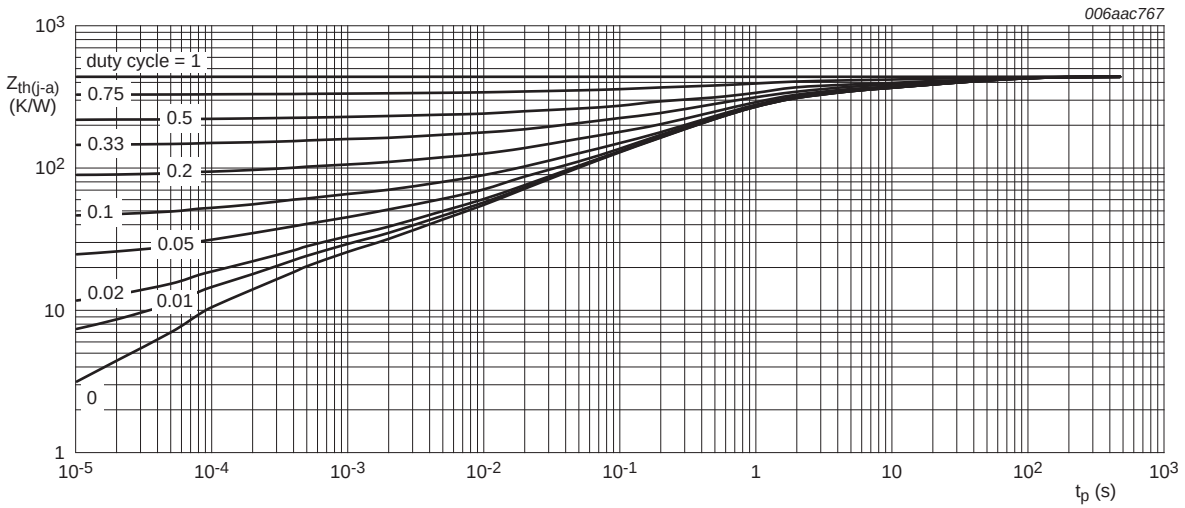
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]				
	PEMD3 (SOT666)			-	-	625	K/W
	PIMD3 (SOT457)			-	-	500	K/W
	PUMD3 (SOT363)			-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]				
	PEMD3 (SOT666)			-	-	417	K/W
	PIMD3 (SOT457)			-	-	313	K/W
	PUMD3 (SOT363)			-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



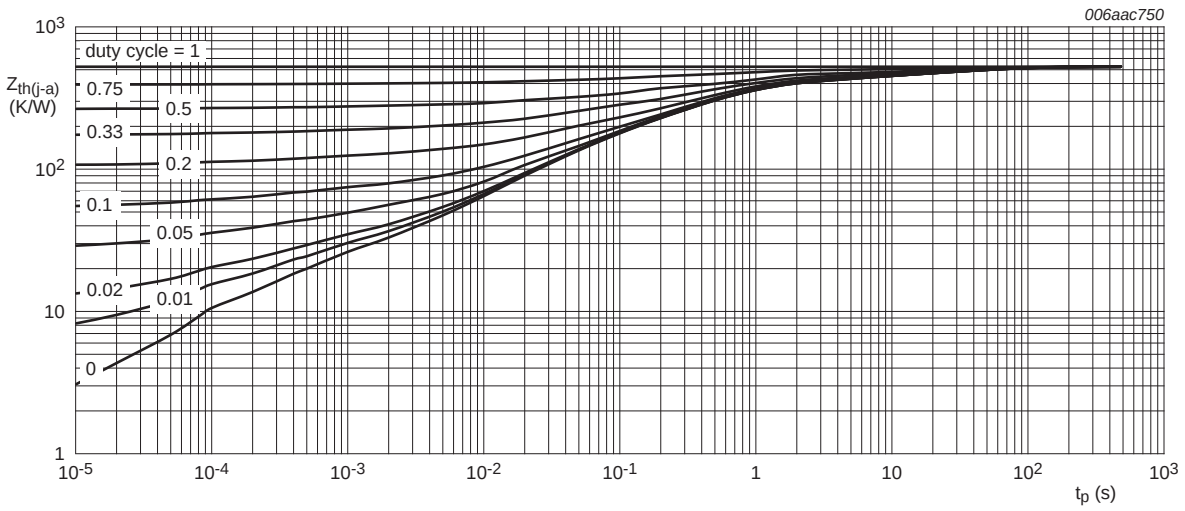
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMD3 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PIMD3 (SOT457); typical values



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMD3 (SOT363); typical values

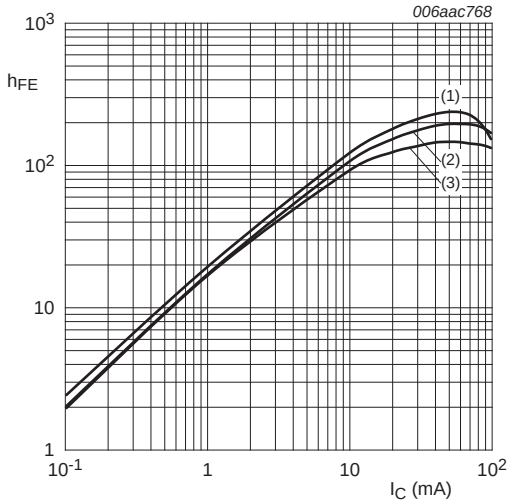
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor; for the PNP transistor (TR2) with negative polarity							
I_{CBO}	collector-base cut-off current	V_{CB} = 50 V; I_E = 0 A		-	-	100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 30 V; I_B = 0 A		-	-	1	μA
		V_{CE} = 30 V; I_B = 0 A; T_j = 150 °C		-	-	5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A		-	-	400	μA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 5 mA		30	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_C = 100 μA		-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_C = 10 mA		2.5	1.8	-	V
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C_c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz					
	TR1 (NPN)			-	-	2.5	pF
	TR2 (PNP)			-	-	3	pF
f_T	transition frequency	V_{CB} = 5 V; I_C = 10 mA; f = 100 MHz	[1]				
	TR1 (NPN)			-	230	-	MHz
	TR2 (PNP)			-	180	-	MHz

[1] Characteristics of built-in transistor.



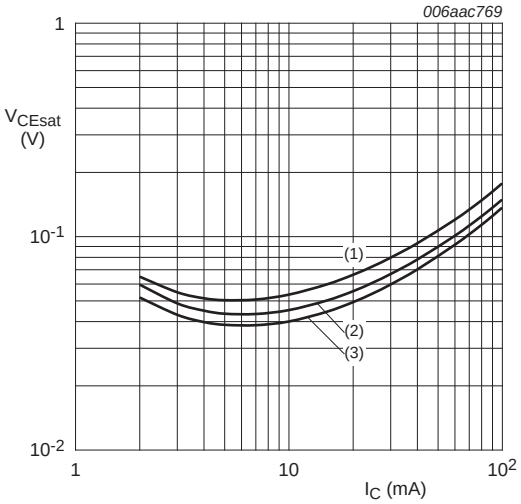
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 5. TR1 (NPN): DC current gain as a function of collector current; typical values



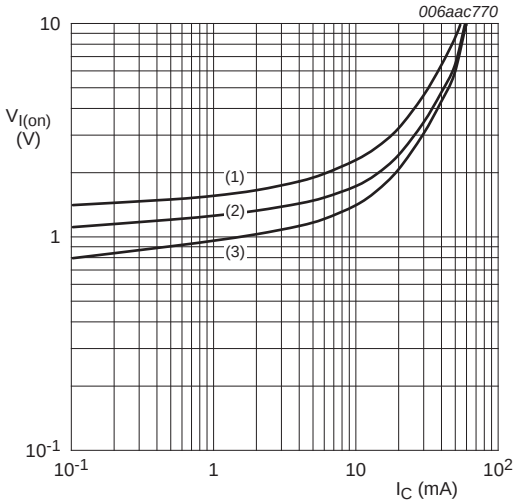
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 6. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



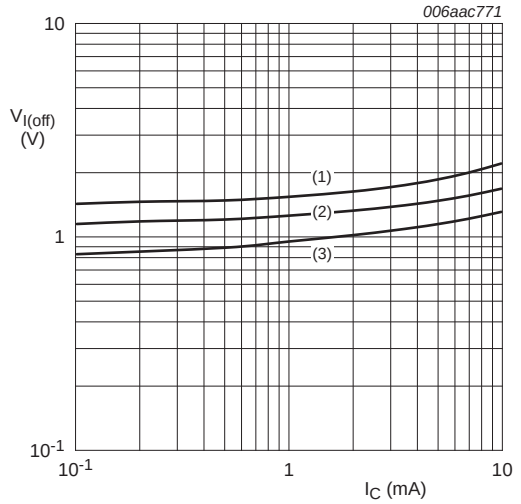
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 7. TR1 (NPN): On-state input voltage as a function of collector current; typical values



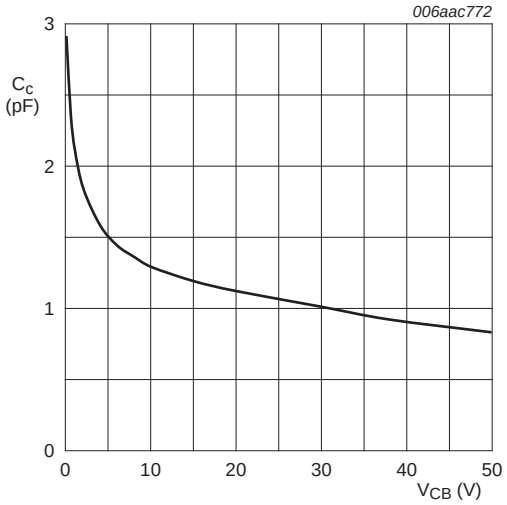
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

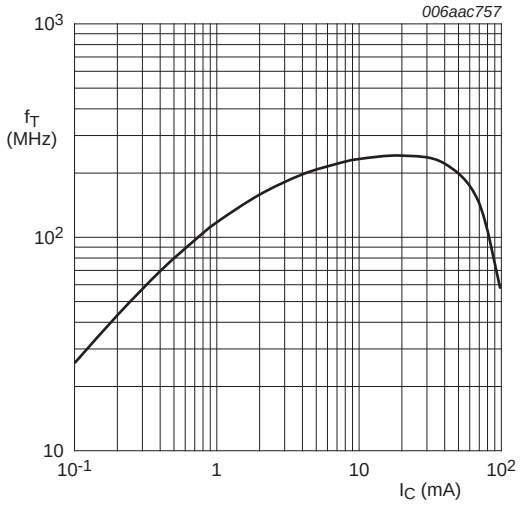
(3) T_{amb} = 100 °C

Fig 8. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



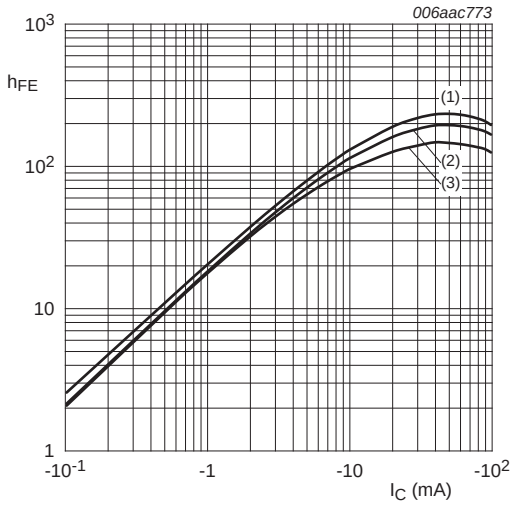
f = 1 MHz; T_{amb} = 25 °C

Fig 9. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 10. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



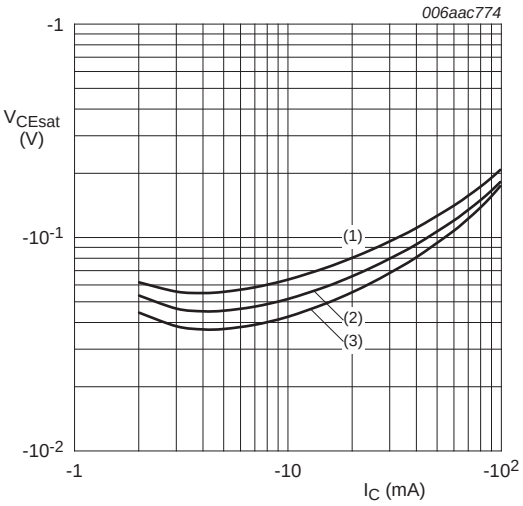
V_{CE} = −5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 11. TR2 (PNP): DC current gain as a function of collector current; typical values



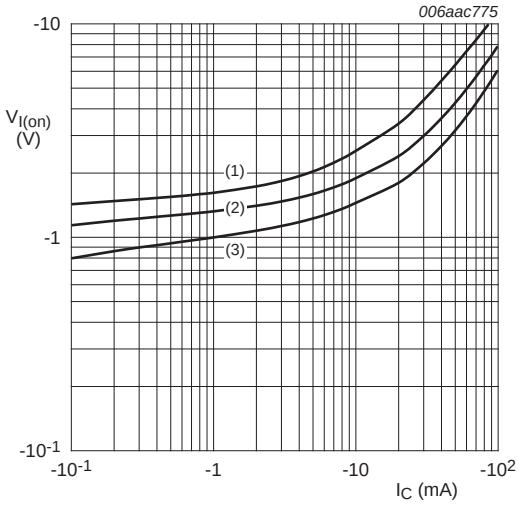
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 12. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



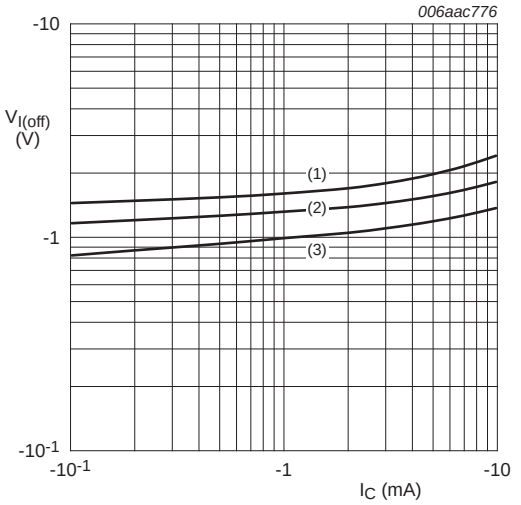
V_{CE} = –0.3 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 13. TR2 (PNP): On-state input voltage as a function of collector current; typical values



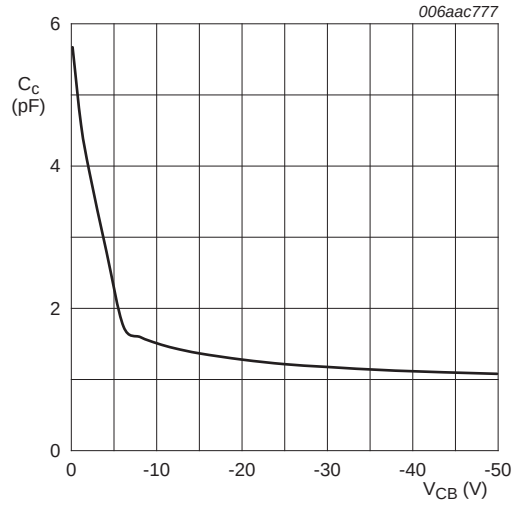
V_{CE} = –5 V

(1) T_{amb} = –40 °C

(2) T_{amb} = 25 °C

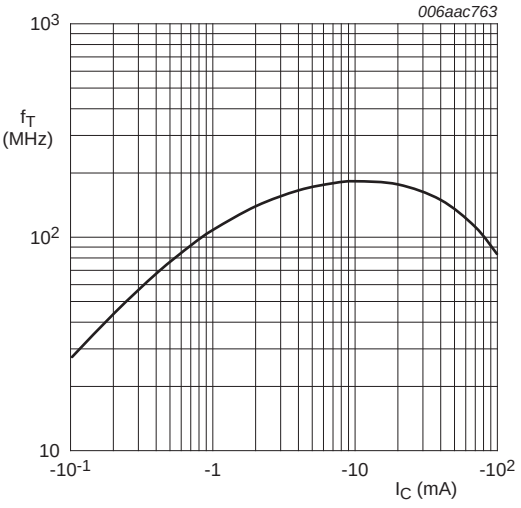
(3) T_{amb} = 100 °C

Fig 14. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = –5 V; T_{amb} = 25 °C

Fig 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

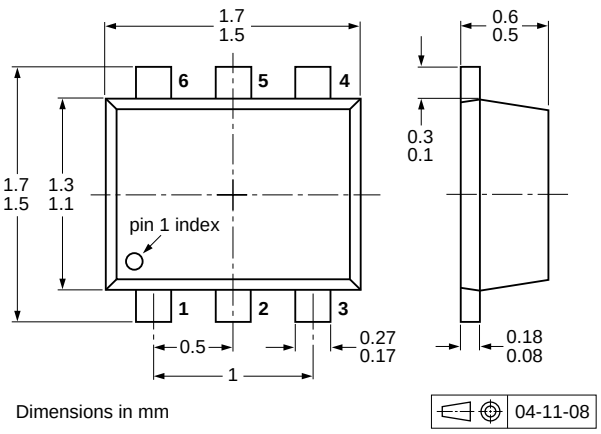


Fig 17. Package outline PEMD3 (SOT666)

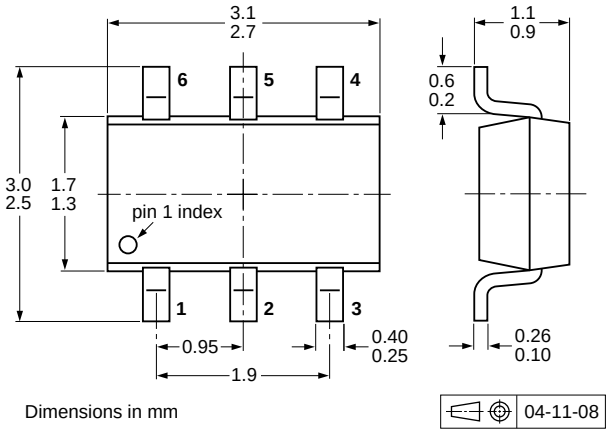


Fig 18. Package outline PIMD3 (SOT457/SC-74)

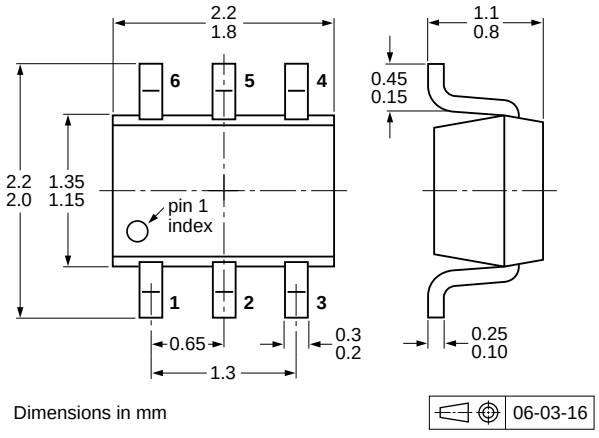


Fig 19. Package outline PUMD3 (SOT363/SC-88)

10. Soldering

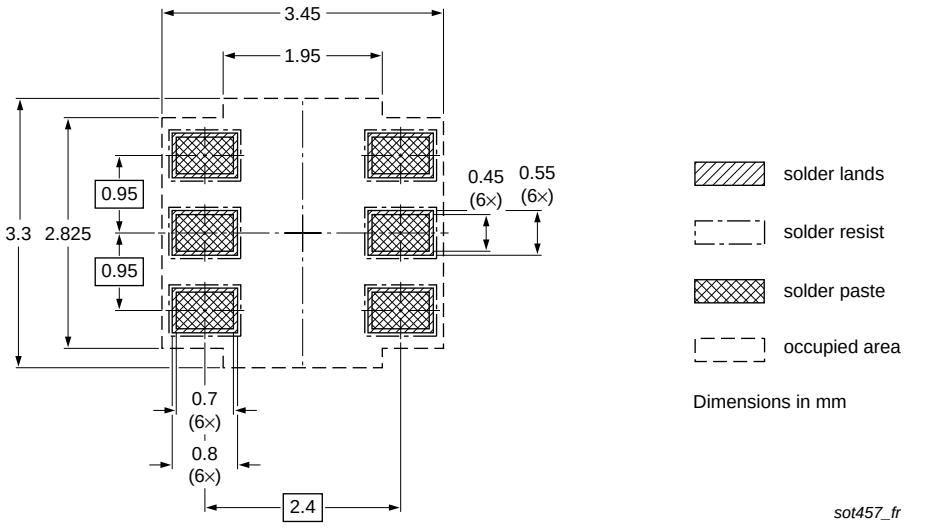


Fig 20. Reflow soldering footprint PIMD3 (SOT457/SC-74)

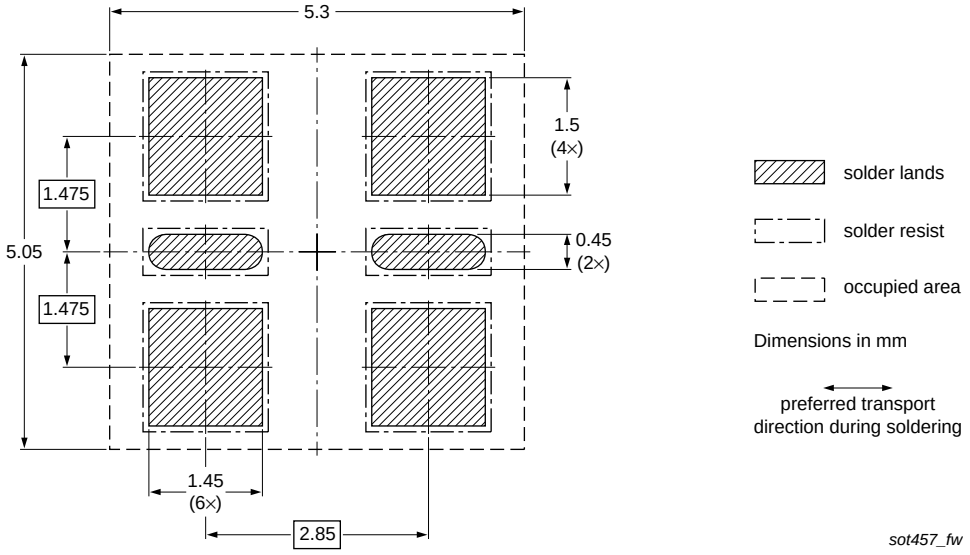


Fig 21. Wave soldering footprint PIMD3 (SOT457/SC-74)

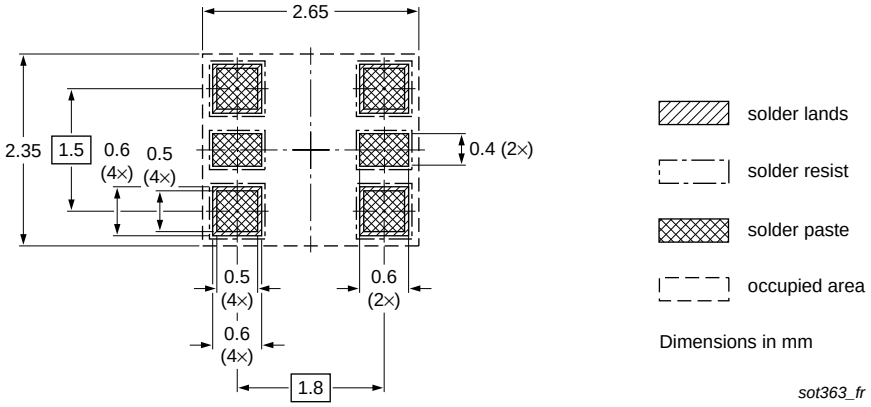


Fig 22. Reflow soldering footprint PUMD3 (SOT363/SC-88)

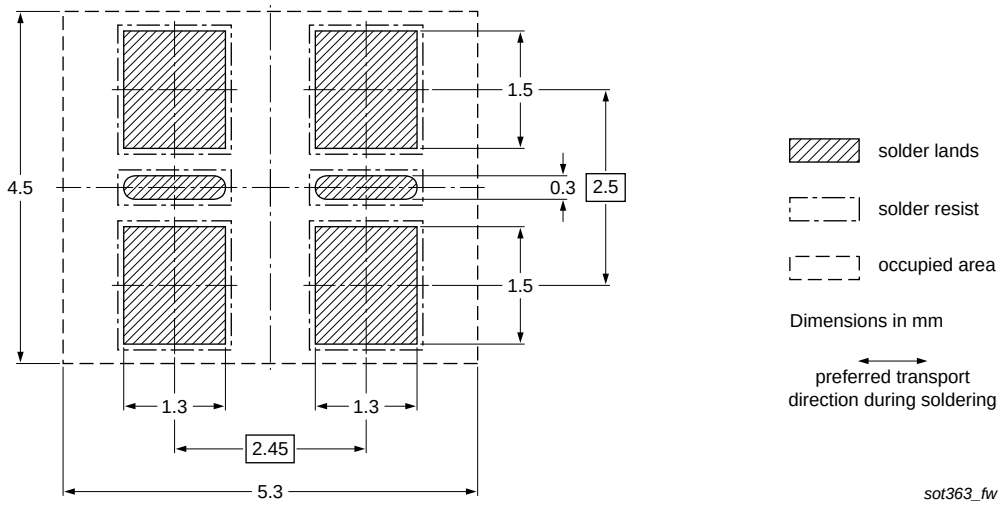


Fig 23. Wave soldering footprint PUMD3 (SOT363/SC-88)

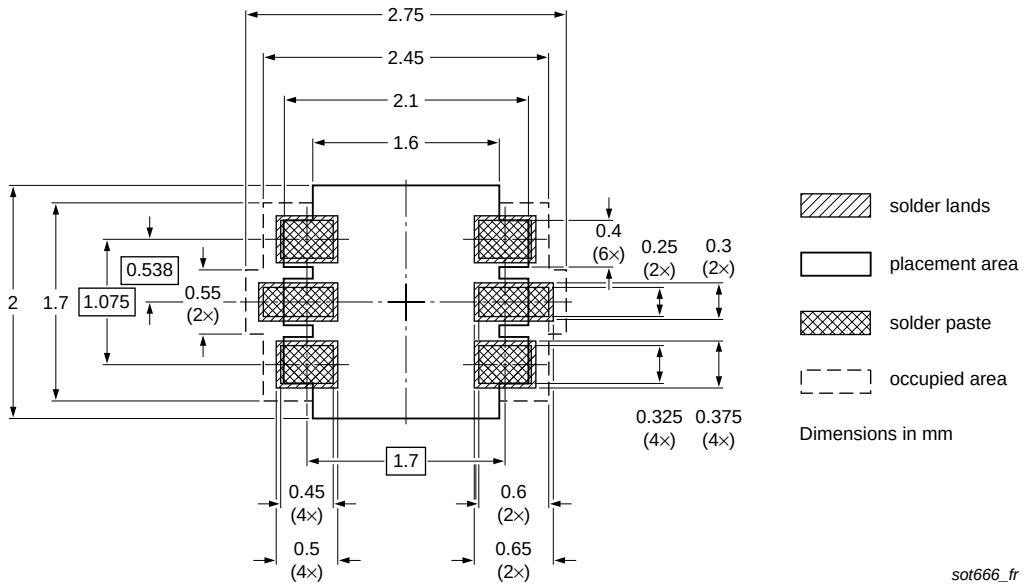


Fig 24. Reflow soldering footprint PEMD3 (SOT666)

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD3_PIMD3_ PUMD3 v.11	20130925	Product data sheet	-	PEMD3_PIMD3_ PUMD3 v.10
Modifications:	• Section 1 “Product profile”: updated • Section 4 “Marking”: updated • Table 6 “Limiting values”: P_{tot} updated according to the latest measurements • Table 7 “Thermal characteristics”: updated according to the latest measurements • Table 8 “Characteristics”: I_{CEO} updated according to the latest measurements, f_T added • Figure 1 to 3, 9, 10, 15 and 16: added • Figure 5 to 8 and Figure 11 to 14: updated • Section 8 “Test information”: added • Section 10 “Soldering”: added • Section 12 “Legal information”: updated			
PEMD3_PIMD3_ PUMD3 v.10	20091115	Product data sheet	-	PEMD3_PIMD3_ PUMD3 v.9
PEMD3_PIMD3_ PUMD3 v.9	20050518	Product data sheet	-	PEMD3_PIMD3_ PUMD3 v.8
PEMD3_PIMD3_ PUMD3 v.8	20041206	Product data sheet	-	PEMD3_PUMD3 v.7

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

14. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 25 September 2013
Document identifier: PEMD3_PIMD3_PUMD3

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased ***category:***

Click to view products by NXP ***manufacturer:***

Other Similar products are found below :

MMUN2217LT1G FP101-TL-E RN1607(TE85L,F) DRC9A14E0L DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143TF3T5G NSBA143ZF3T5G NSBC114EF3T5G NSBC114YF3T5G NSBC123TF3T5G NSBC143TF3T5G NSVMUN2212T1G NSVMUN5111DW1T3G NSVMUN5314DW1T3G NSVUMC2NT1G SMMUN2134LT1G SMUN2212T1G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G 2SC3650-TD-E RN1303(TE85L,F) RN4605(TE85L,F) BCR135SH6327XT TTEPROTOTYPE79 UMC3NTR DTA113EET1G EMA2T2R EMH15T2R SDTA114YET1G SMMUN2111LT3G SMMUN2113LT1G SMMUN2114LT1G SMMUN2211LT3G SMUN2214T3G SMUN5113DW1T1G SMUN5335DW1T1G NSBA114YF3T5G NSBC114TF3T5G